

894 ED	$\text{C}_{10}\text{H}_{27}\text{GaSi}_3$		[Tris(trimethylsilyl)methyl]gallium		C_3 assumed $\text{GaC}(\text{Si}(\text{CH}_3)_3)_3$
	r_a	$\text{\AA}^a)$	θ_a	$\text{deg}^a)$	
	Ga–C* ^{b)}	2.064(17)	Ga–C*–Si ^{b)}	106.2(9)	
	C*–Si ^{b)}	1.882(16)	Si–C*–Si ^{b)}	112.5(8)	
	Si–C	1.893(7)	C–Si–C	104.6(7)	
	C–H	1.107(4)	Si–C–H	112.8(9)	
			$\tau(\text{Ga–C*–Si–C})^b)^c)$	43(2)	
			$\tau(\text{C*–Si–C–H})^b)^c)$	56(31)	
			tilt[Si(CH ₃) ₃] ^{d)}	1.2(13)	

Local C_3 symmetry for each $\text{Si}(\text{CH}_3)_3$ group and local C_{3v} symmetry for each SiCH_3 fragment were assumed.

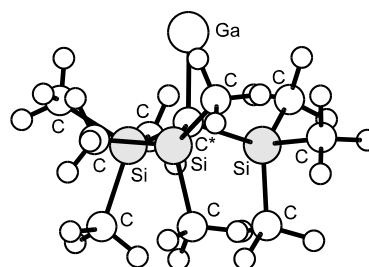
The nozzle temperatures were *ca.* 150 and 200 °C.

^{a)} Twice the estimated standard errors including an estimated scale error.

^{b)} C* denotes the central carbon atom.

^{c)} $\tau = 0^\circ$ for the *syn* position.

^{d)} Tilt angle is positive when the symmetry axis of the $\text{Si}(\text{CH}_3)_3$ group intersects the molecular symmetry axis below C*.



Haaland, A., Martinsen, K.-G., Volden, H.V., Kaim, W., Waldhör, E., Uhl, W., Schütz, U.: *Organometallics* **15** (1996) 1146.